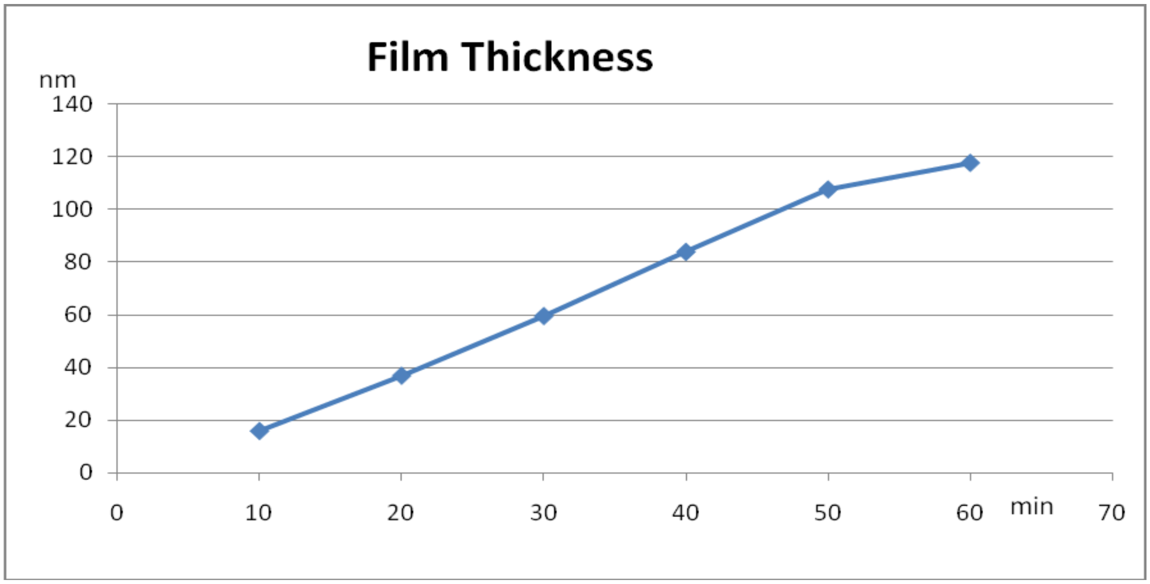
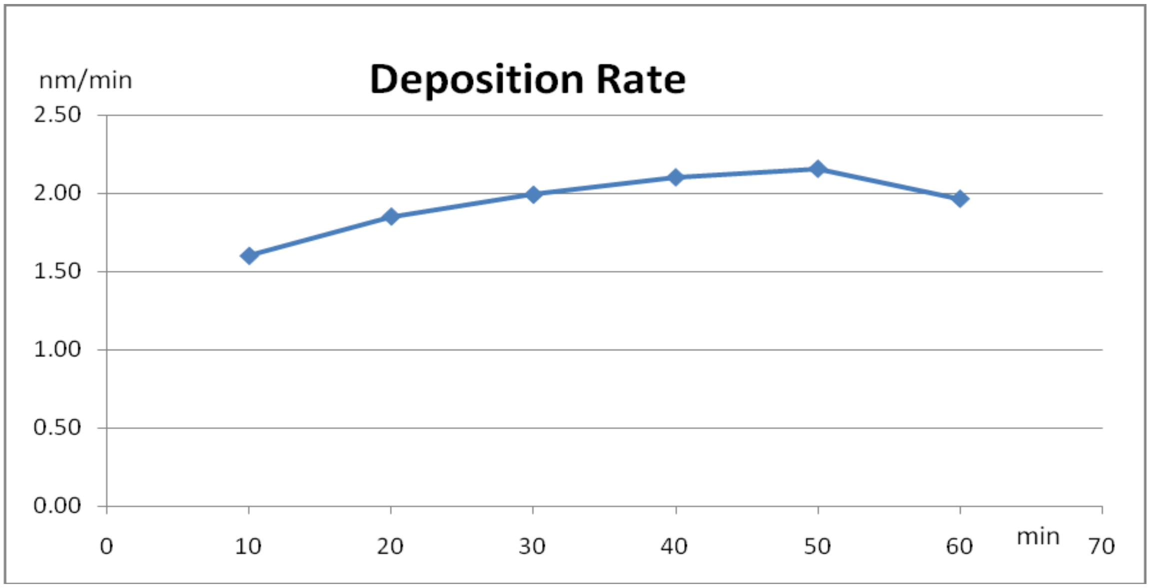
LPCVD	**Tube 1**	**Material**	**Silicon Nitride**	
Uniformity:	Film Uniformity Variance < 2% across 4” wafer			
Gases	**Flow Rate**	**Time(minutes)**	**Film Thickness(nm)**	**Deposition Rate(nm/min)**
Temperature	750 C	10	16	1.60
Comments:		20	37	1.85
		30	59.66	1.99
		40	84	2.10
		50	107.7	2.15
		60	117.8	1.96





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